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					ez 11			
			FC-MCP	Si Interposer	Embedded Si Interposer	Organic Interposer	3D IC	
	Dielectri Properti	c es	Good	Lossy	Lossy	Good	Lossy	
	Feature Dimensi	ons	Down to ~ 10um L/S	BEOL interconnects	BEOL interconnects	Down to ~ 5um L/S	BEOL interconnects	
	CTE Mismato	h	Mod. High	Excellent	Mod. High	Mod. High	Excellent	
	Cost		Moderate	Moderate	TBD	Moderate	High	
	Availabi Supply Chain	lity /	Available	Available	Development	Development	Development	
	From Substrate Based to Wafer Level System Integration					ation referred. Class Muller. 22		

Features	Organic Internoser	Silicon Internoser
Cu Wiring (Dielectrics)	Semi-Additive Process (Polyimide)	Damascene (Oxide)
Dielectric Properties	Good	Lossy
uBump Material	Cu/Ni/SnAg etc.	Cu/Ni/SnAg etc.
uBump Size / Pitch (min)	30 / 55 um	20 / 55 um
Front Side Cu wiring Line / Space / Thickness (min)	6 / 6 / 10 um	0.5 / 0.5 / 1.0 um
Via Size in Cu Wiring Layers	20 um	1.0 um
Through Interposer Via or TSV Diameter / Pitch / Thickness	60 / 150 / 200 um	10 / 50 /100 um
Bottom Side Cu wiring Line / Space / Thickness (min)	6 / 6 / 10 um	10 / 10 / 3um
Bottom Side Pad or Bump Size / Pitch (typical)	Ni/Au 100 / 150 um	Ni/Au etc. 100 / 150 um





